

- One Line Receiver and Eight Line Drivers Configured as an 8-Port LVDS Repeater
- Line Receiver and Line Drivers Meet or Exceed the Requirements of ANSI EIA/TIA-644 Standard
- Designed for Signaling Rates up to 622 Mbps
- Enabling Logic Allows Individual Control of Each Driver Output, Plus all Outputs
- Low-Voltage Differential Signaling With Typical Output Voltage of 350 mV and a 100Ω Load
- Electrically Compatible With LVDS, PECL, LVPECL, LVTTTL, LVCMOS, GTL, BTL, CTT, SSTL, or HSTL Outputs With External Termination Networks
- Propagation Delay Times < 4.7 ns
- Output Skew Less Than 300 ps and Part-to-Part Skew Less Than 1.5 ns
- Total Power Dissipation at 200 MHz Typically Less Than 330 mW With 8 Channels Enabled
- Driver Outputs or Receiver Input Equals High Impedance When Disabled or With $V_{CC} < 1.5$ V
- Bus-Pin ESD Protection Exceeds 12 kV
- Packaged in Thin Shrink Small-Outline Package With 20-mil Terminal Pitch

DBT PACKAGE
(TOP VIEW)

GND	1	38	ANC
V _{CC}	2	37	AY
GND	3	36	AZ
NC	4	35	BY
ENM	5	34	BZ
ENA	6	33	CY
ENB	7	32	CZ
ENC	8	31	DY
END	9	30	DZ
A	10	29	EY
B	11	28	EZ
ENE	12	27	FY
ENF	13	26	FZ
ENG	14	25	GY
ENH	15	24	GZ
NC	16	23	HY
GND	17	22	HZ
V _{CC}	18	21	NC
GND	19	20	NC

description

The SN65LVDS108 is configured as one differential line receiver connected to eight differential line drivers. Individual output enables are provided for each output and an additional enable is provided for all outputs.

The line receivers and line drivers implement the electrical characteristics of low-voltage differential signaling (LVDS). LVDS, as specified in EIA/TIA-644, is a data signaling technique that offers low power, low noise emission, high noise immunity, and high switching speeds. It can be used to transmit data at speeds up to at least 622 Mbps and over relatively long distances. (Note: The ultimate rate and distance of data transfer is dependent upon the attenuation characteristics of the media, the noise coupling to the environment, and other system characteristics.)

The intended application of this device, and the LVDS signaling technique, is for point-to-point or point-to-multipoint (distributed simplex) baseband data transmission on controlled impedance media of approximately 100 Ω. The transmission media may be printed-circuit board traces, backplanes, or cables. The large number of drivers integrated into the same silicon substrate, along with the low pulse skew of balanced signaling, provides extremely precise timing alignment of the signals being repeated from the inputs. This is particularly advantageous for implementing system clock or data distribution trees.

The SN65LVDS108 is characterized for operation from –40°C to 85°C.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

 **TEXAS
INSTRUMENTS**

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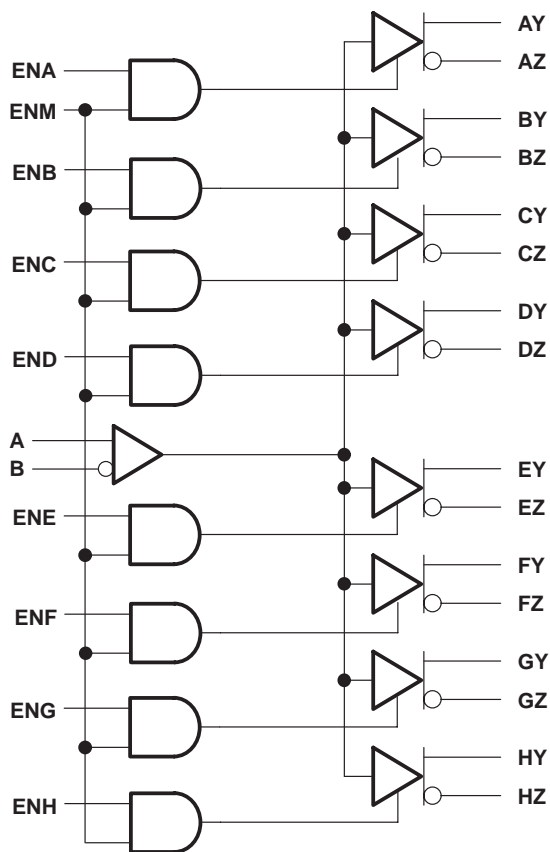
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SN65LVDS108

8-PORT LVDS REPEATER

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logic diagram (positive logic)



selection guide to LVDS splitter

The SN65LVDS108 is one member of a family of LVDS splitters and repeaters. A brief overview of the family is provided in the following table.

LVDS SPLITTER AND REPEATER FAMILY

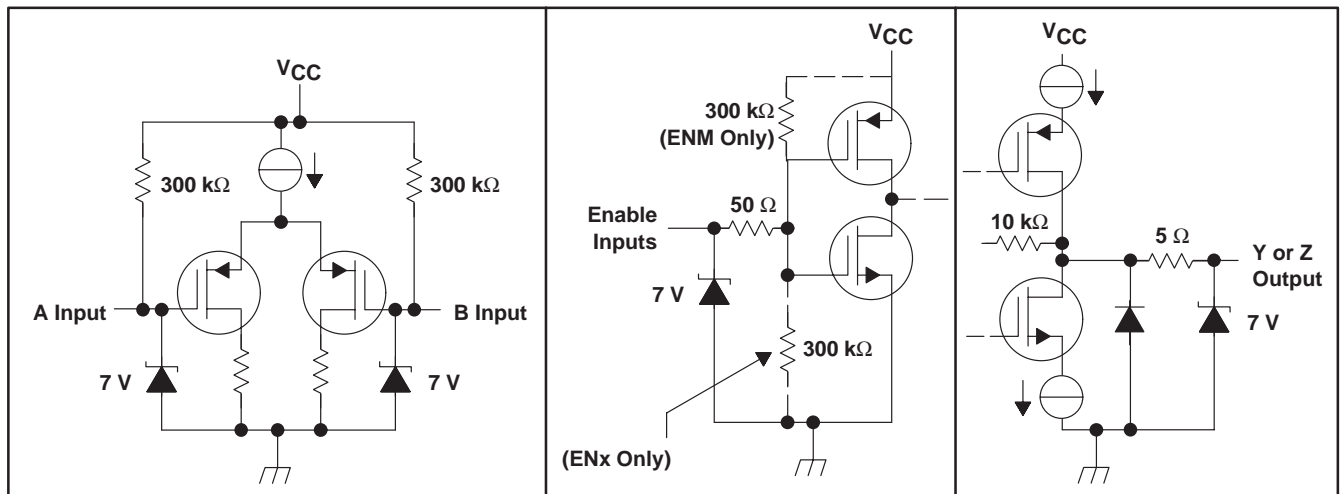
DEVICE	NUMBER OF INPUTS	NUMBER OF OUTPUTS	PACKAGE	COMMENTS
SN65LVDS104	1 LVDS	4 LVDS	16-pin D	4-Port LVDS Repeater
SN65LVDS105	1 LVTTTL	4 LVDS	16-pin D	4-Port TTL-to-LVDS Repeater
SN65LVDS108	1 LVDS	8 LVDS	38-pin DBT	8-Port LVDS Repeater
SN65LVDS109	2 LVDS	8 LVDS	38-pin DBT	Dual 4-Port LVDS Repeater
SN65LVDS116	1 LVDS	16 LVDS	64-pin DGG	16-Port LVDS Repeater
SN65LVDS117	2 LVDS	16 LVDS	64-pin DGG	Dual 8-Port LVDS Repeater

FUNCTION TABLE

INPUTS			OUTPUTS	
$V_{ID} = V_A - V_B$	ENM	ENx	\overline{xY}	\overline{xZ}
X	L	X	Z	Z
X	X	L	Z	Z
$V_{ID} \geq 100 \text{ mV}$	H	H	H	L
$-100 \text{ mV} < V_{ID} < 100 \text{ mV}$	H	H	?	?
$V_{ID} \leq -100 \text{ mV}$	H	H	L	H

H = high level, L = low level, Z = high impedance, X = don't care,
? = indeterminate

equivalent input and output schematic diagrams



absolute maximum ratings over operating free-air temperature (unless otherwise noted)[†]

Supply voltage range, V_{CC} (see Note 1)	–0.5 V to 4 V
Input voltage range, Enable inputs	–0.5 V to 6 V
A, B, Y or Z	–0.5 V to 4 V
Electrostatic discharge, Y, Z, and GND (see Note 2)	Class 3, A: 12 kV, B: 500 V
All pins	Class 3, A: 4 kV, B: 400 V
Continuous power dissipation	See Dissipation Rating Table
Storage temperature range	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
2. Tested in accordance with MIL-STD-883C Method 3015.7.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR [‡] ABOVE $T_A = 25^\circ\text{C}$	$T_A = 85^\circ\text{C}$ POWER RATING
DBT	1277 mW	10.2 mW/°C	644 mW

[‡] This is the inverse of the junction-to-ambient thermal resistance when board-mounted (low-k) with no air flow.

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recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V_{CC}	3	3.3	3.6	V
High-level input voltage, V_{IH}	2			V
Low-level input voltage, V_{IL}			0.8	V
Magnitude of differential input voltage, $ V_{ID} $	0.1		3.6	V
Common-mode input voltage, V_{IC}	$\frac{ V_{ID} }{2}$		$2.4 - \frac{ V_{ID} }{2}$	V
			$V_{CC} - 0.8$	V
Operating free-air temperature, T_A	-40		85	°C

electrical characteristics over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
V_{ITH+} Positive-going differential input voltage threshold	See Figure 1 and Table 1			100	mV
V_{ITH-} Negative-going differential input voltage threshold		-100			
$ V_{OD} $ Differential output voltage magnitude	$R_L = 100\ \Omega$, $V_{ID} = \pm 100\text{ mV}$, See Figure 1 and Figure 2	247	340	454	mV
$\Delta V_{OD} $ Change in differential output voltage magnitude between logic states		-50		50	
$V_{OC(SS)}$ Steady-state common-mode output voltage	See Figure 3	1.125		1.375	V
$\Delta V_{OC(SS)}$ Change in steady-state common-mode output voltage between logic states		-50		50	mV
$V_{OC(PP)}$ Peak-to-peak common-mode output voltage			50	150	
I_{CC} Supply current	Enabled, $R_L = 100\ \Omega$		62	85	mA
	Disabled		8	12	
I_I Input current (A or B inputs)	$V_I = 0\text{ V}$	-2		-20	μA
	$V_I = 2.4\text{ V}$	-1.2			
$I_{I(OFF)}$ Power-off input current (A or B inputs)	$V_{CC} = 1.5\text{ V}$, $V_I = 2.4\text{ V}$			20	μA
I_{IH} High-level input current (enables)	$V_{IH} = 2\text{ V}$			± 20	μA
I_{IL} Low-level input current (enables)	$V_{IL} = 0.8\text{ V}$			± 10	μA
I_{OS} Short-circuit output current	V_{OY} or $V_{OZ} = 0\text{ V}$			± 24	mA
	$V_{OD} = 0\text{ V}$			± 12	
I_{OZ} High-impedance output current	$V_O = 0\text{ V}$ or V_{CC}			± 1	μA
$I_{O(OFF)}$ Power-off output current	$V_{CC} = 1.5\text{ V}$, $V_O = 3.6\text{ V}$			± 1	μA
C_{IN} Input capacitance (A or B inputs)	$V_I = 0.4 \sin(4E6\pi t) + 0.5\text{ V}$		5		pF
C_O Output capacitance (Y or Z outputs)	$V_I = 0.4 \sin(4E6\pi t) + 0.5\text{ V}$, Disabled		9.4		

† All typical values are at 25°C and with a 3.3 V supply.

switching characteristics over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output	R _L = 100 Ω, C _L = 10 pF, See Figure 4	1.6	2.8	4.5	ns
t _{PHL}	Propagation delay time, high-to-low-level output		1.6	2.8	4.5	
t _r	Differential output signal rise time		0.3	0.8	1.2	ns
t _f	Differential output signal fall time		0.3	0.8	1.2	
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})‡			150	500	ps
t _{sk(o)}	Output skew§				300	
t _{sk(pp)}	Part-to-part skew#				1.5	ns
t _{PZH}	Propagation delay time, high-impedance-to-high-level output	See Figure 5		5.7	15	ns
t _{PZL}	Propagation delay time, high-impedance-to-low-level output			7.7	15	
t _{PHZ}	Propagation delay time, high-level-to-high-impedance output			3.2	15	ns
t _{PLZ}	Propagation delay time, low-level-to-high-impedance output			3.2	15	

† All typical values are at 25°C and with a 3.3 V supply.

‡ t_{sk(p)} is the magnitude of the time difference between the t_{PLH} and t_{PHL} of any output of a single device.

§ t_{sk(o)} is the magnitude of the time difference between the t_{PLH} or t_{PHL} measured at any two outputs.

t_{sk(pp)} is the magnitude of the time difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

PARAMETER MEASUREMENT INFORMATION

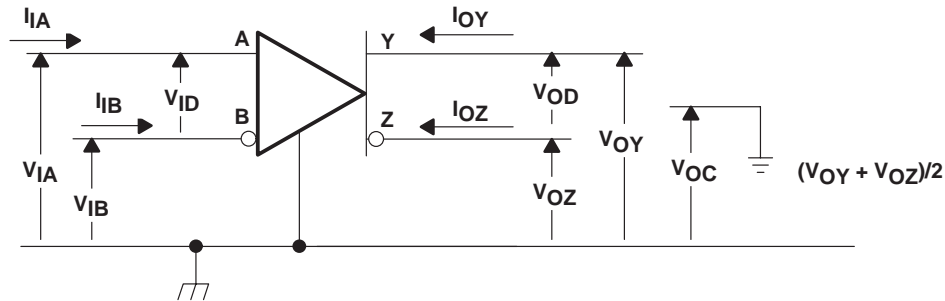


Figure 1. Voltage and Current Definitions

PARAMETER MEASUREMENT INFORMATION

Table 1. Receiver Minimum and Maximum Input Threshold Test Voltages

APPLIED VOLTAGES		RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON-MODE INPUT VOLTAGE
V_{IA}	V_{IB}	V_{ID}	V_{IC}
1.25 V	1.15 V	100 mV	1.2 V
1.15 V	1.25 V	-100 mV	1.2 V
2.4 V	2.3 V	100 mV	2.35 V
2.3 V	2.4 V	-100 mV	2.35 V
0.1 V	0 V	100 mV	0.05 V
0 V	0.1 V	-100 mV	0.05 V
1.5 V	0.9 V	600 mV	1.2 V
0.9 V	1.5 V	-600 mV	1.2 V
2.4 V	1.8 V	600 mV	2.1 V
1.8 V	2.4 V	-600 mV	2.1 V
0.6 V	0 V	600 mV	0.3 V
0 V	0.6 V	-600 mV	0.3 V

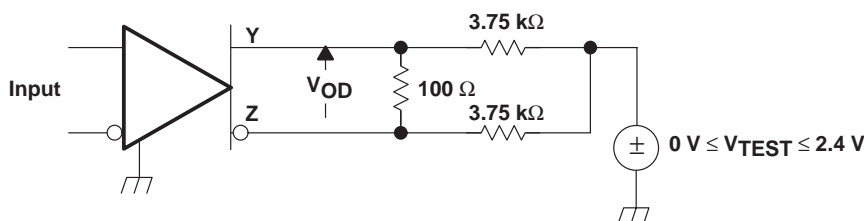
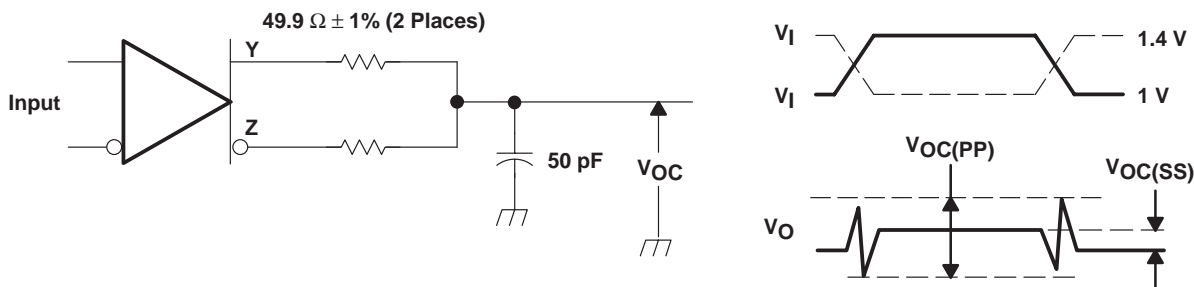


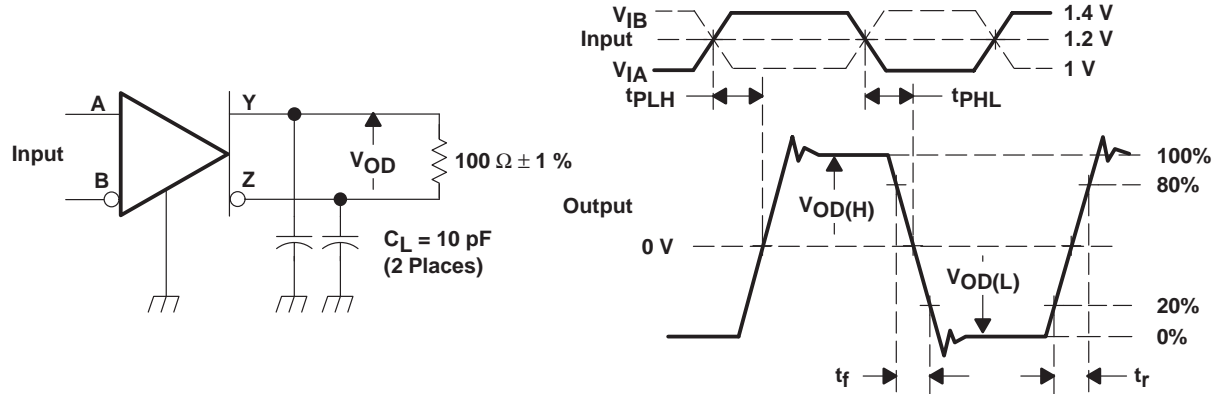
Figure 2. VOD Test Circuit



NOTE A: All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1$ ns, pulse repetition rate (PRR) = 0.5 Mpps, pulsewidth = 500 ± 10 ns. C_L includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T. The measurement of $V_{OC}(PP)$ is made on test equipment with a -3 dB bandwidth of at least 300 MHz.

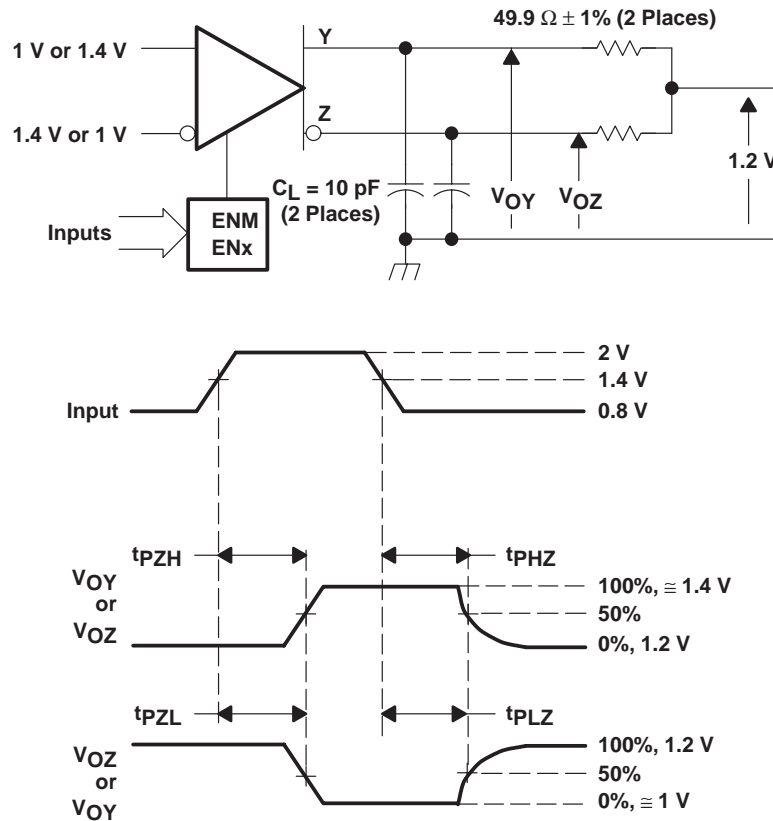
Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage

PARAMETER MEASUREMENT INFORMATION



NOTE A: All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1\text{ ns}$, pulse repetition rate (PRR) = 50 Mpps, pulsewidth = $10 \pm 0.2\text{ ns}$. C_L includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.

Figure 4. Test Circuit, Timing, and Voltage Definitions for the Differential Output Signal



NOTE A: All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1\text{ ns}$, pulse repetition rate (PRR) = 0.5 Mpps, pulsewidth = $500 \pm 10\text{ ns}$. C_L includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.

Figure 5. Enable and Disable Time Circuit and Definitions

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TYPICAL CHARACTERISTICS

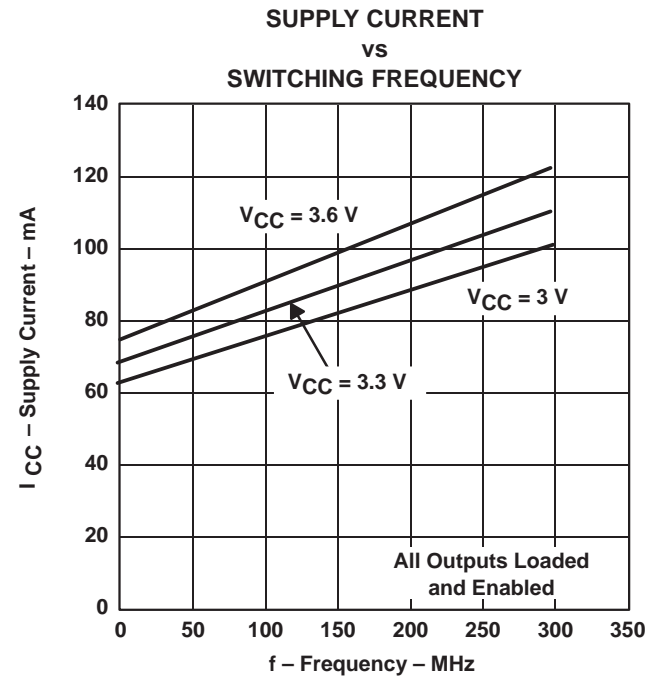


Figure 6

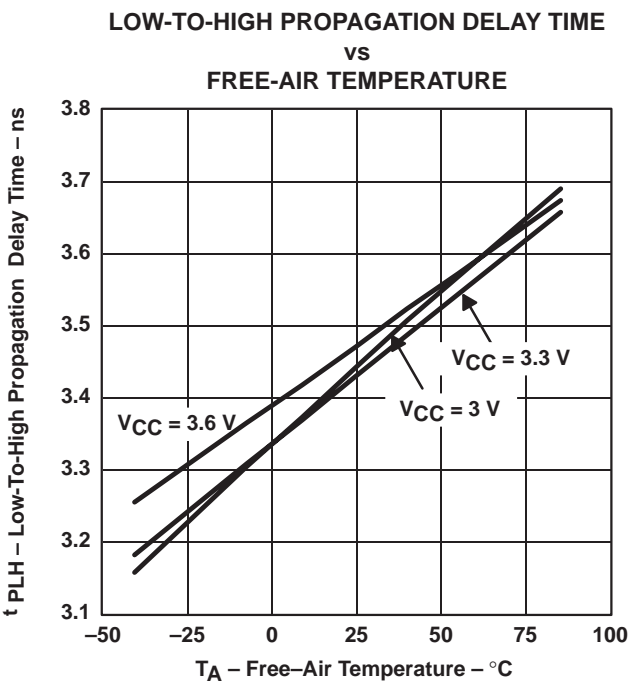


Figure 7

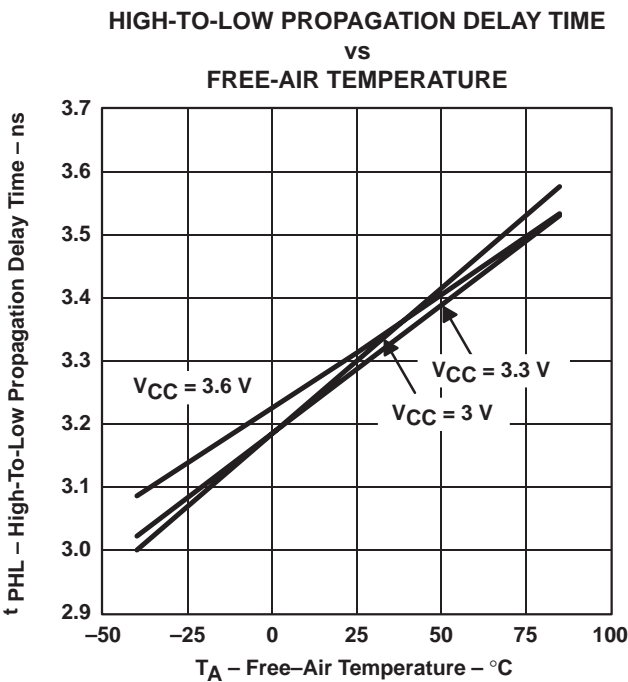


Figure 8

TYPICAL CHARACTERISTICS

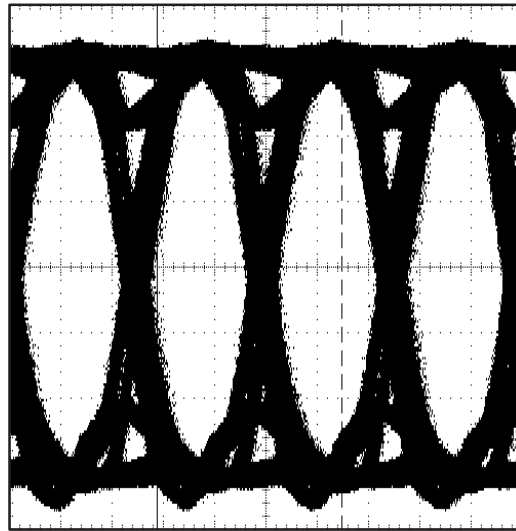


Figure 9. Typical Differential Eye Pattern at 400 Mbps

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APPLICATION INFORMATION

The SN65LVDS108 device solves several problems common to the distribution of timing critical clock and data signals. These problems include:

- Excessive skew between the signal paths
- Noise pickup over long signaling paths
- High power consumption
- Control of which signal paths are enabled or disabled
- Elimination of radiation from unterminated lines

Buffering and splitting the signal on the same silicon die minimizes corruption of the timing relation between the copies of the signal. Buffering and splitting the signal in separate devices will introduce considerably higher levels of uncontrolled timing skew between the signals. Higher speed operation and more timing tolerance for other components of the system is enabled by the tighter system timing budgets provided by the single die implementations of the SN65LVDS108.

The use of LVDS signaling technology for both the inputs and the outputs provides superior common-mode and noise tolerance compared to single-ended I/O technologies. This is particularly important because the signals that are being distributed must be transmitted over longer distances, and at higher rates, than can be accommodated with single-ended I/Os. In addition, LVDS consumes considerably less power than other high-performance differential signaling schemes.

The enable inputs provided for each output may be used to turn on or off any of the paths. This function is required to prevent radiation of signals from the unterminated signal lines on open connectors when boards or devices are being swapped in the end equipment. The individual channel enables are also required if redundant paths are being utilized for reliability reasons.

The following diagram shows how an input signal is being identically repeated out two of the available outputs. A third output is shown in the disabled state.

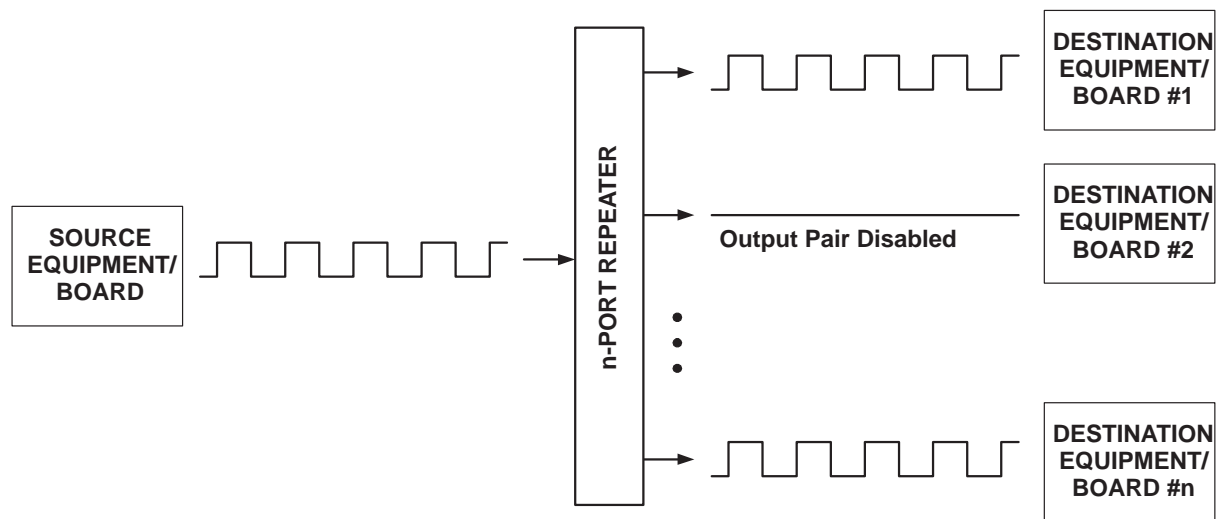


Figure 10. LVDS Repeating Splitter Application Example Showing Individual Path Control

APPLICATION INFORMATION

A LVDS receiver can be used to receive various other types of logic signals. Figure 12 through Figure 20 show the termination circuits for SSTL, HSTL, GTL, BTL, LVPECL, PECL, CMOS, and TTL.

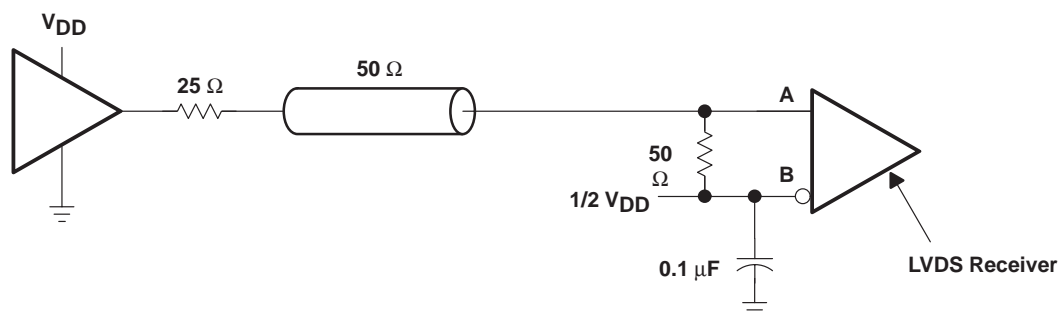


Figure 11. Stub-Series Terminated (SSTL) or High-Speed Transceiver Logic (HSTL)

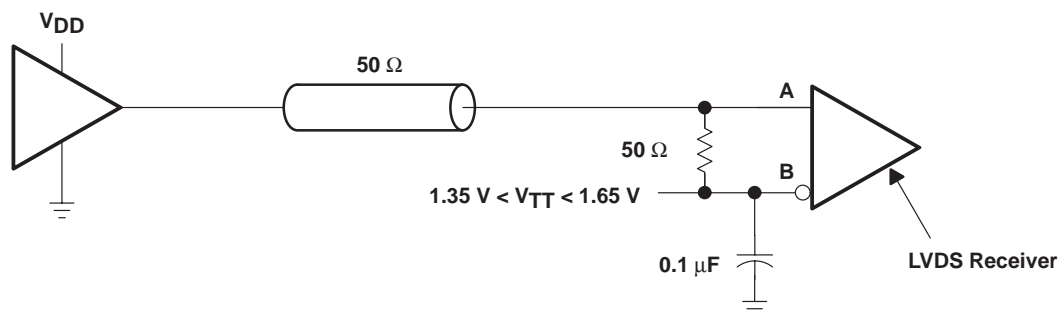


Figure 12. Center-Tap Termination (CTT)

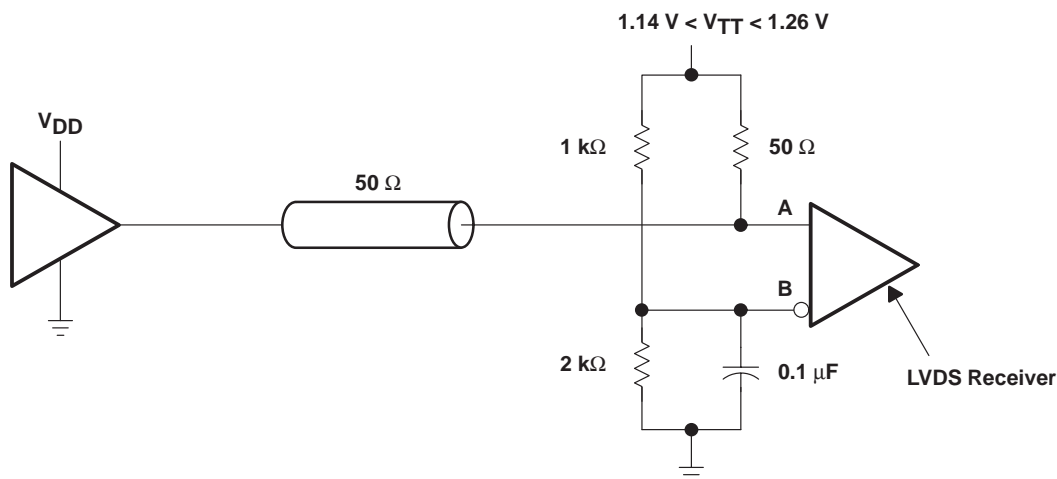


Figure 13. Gunning Transceiver Logic (GTL)

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APPLICATION INFORMATION

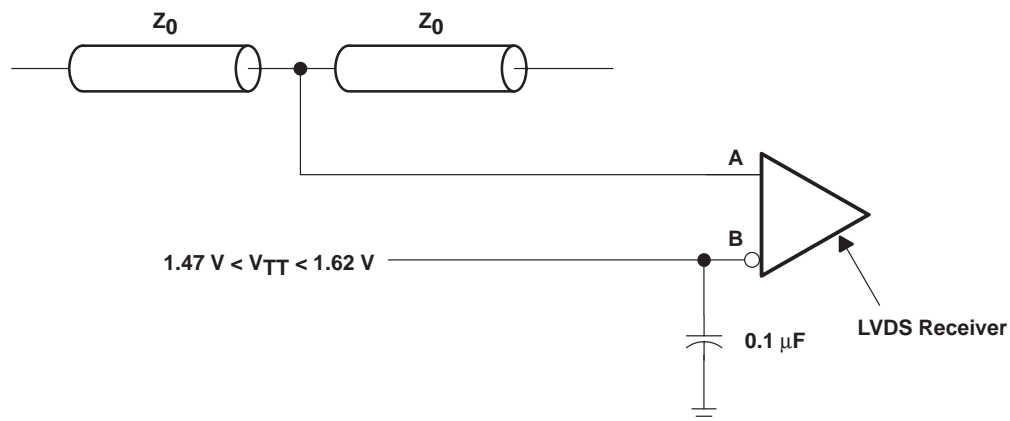


Figure 14. Backplane Transceiver Logic (BTL)

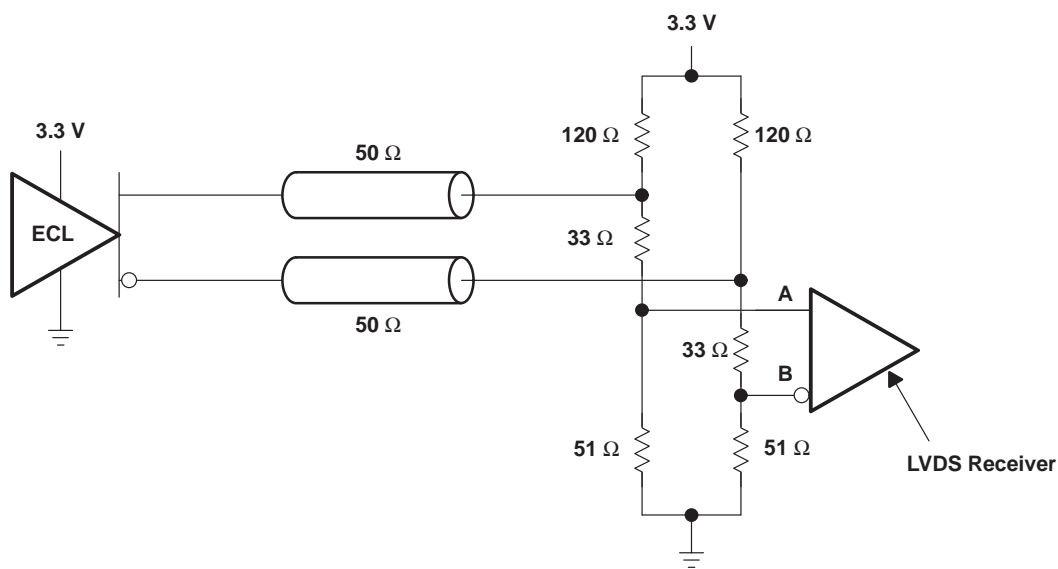


Figure 15. Low-Voltage Positive Emitter-Coupled Logic (LVPECL)

APPLICATION INFORMATION

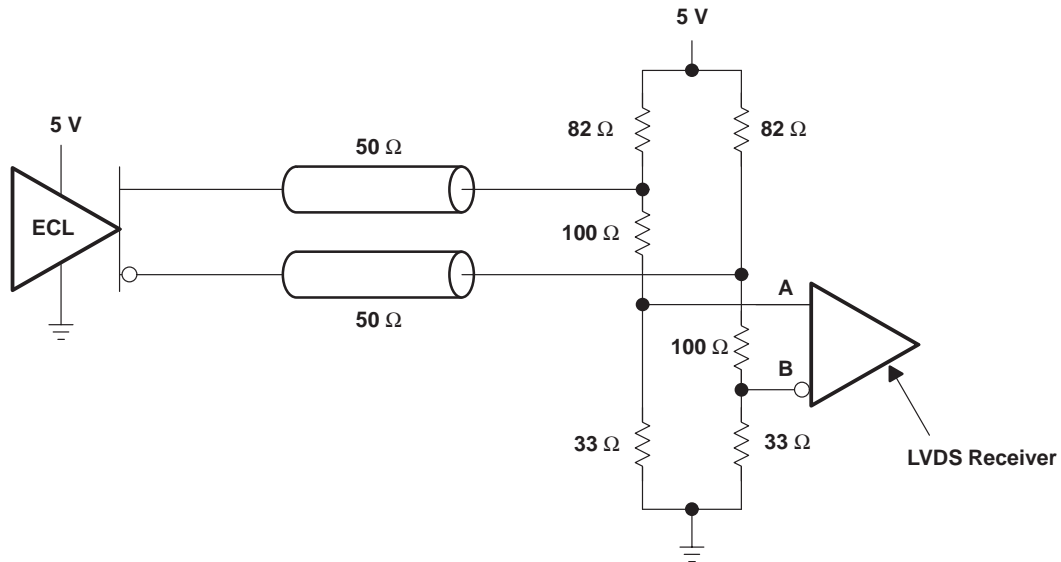


Figure 16. Positive Emitter-Coupled Logic (PECL)

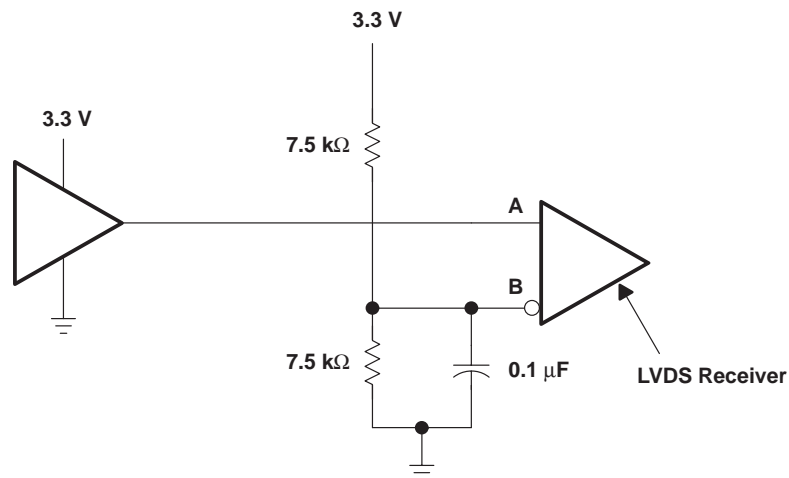


Figure 17. 3.3-V CMOS

APPLICATION INFORMATION

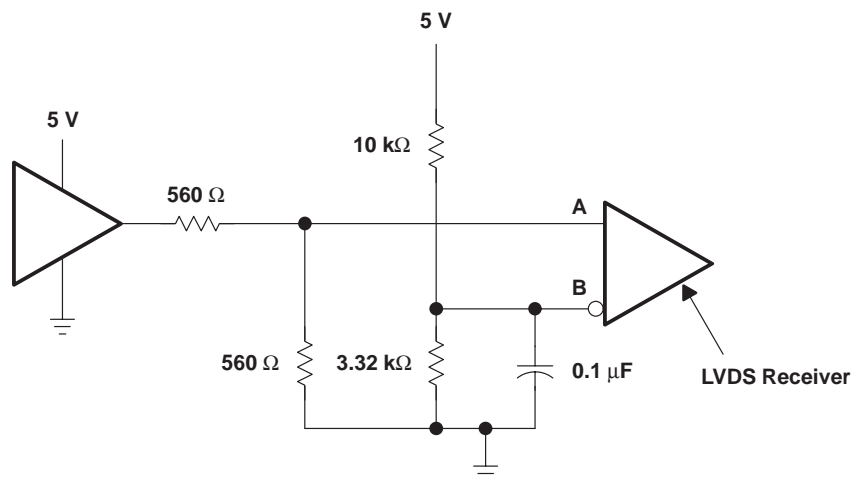


Figure 18. 5-V CMOS

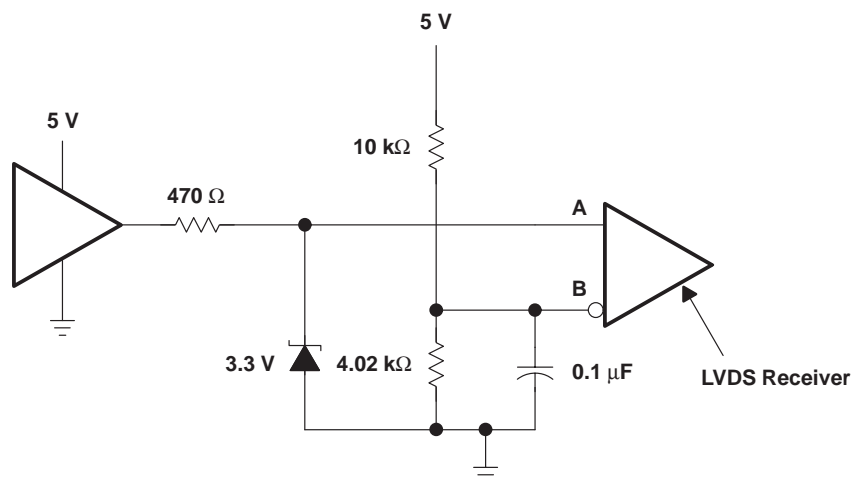


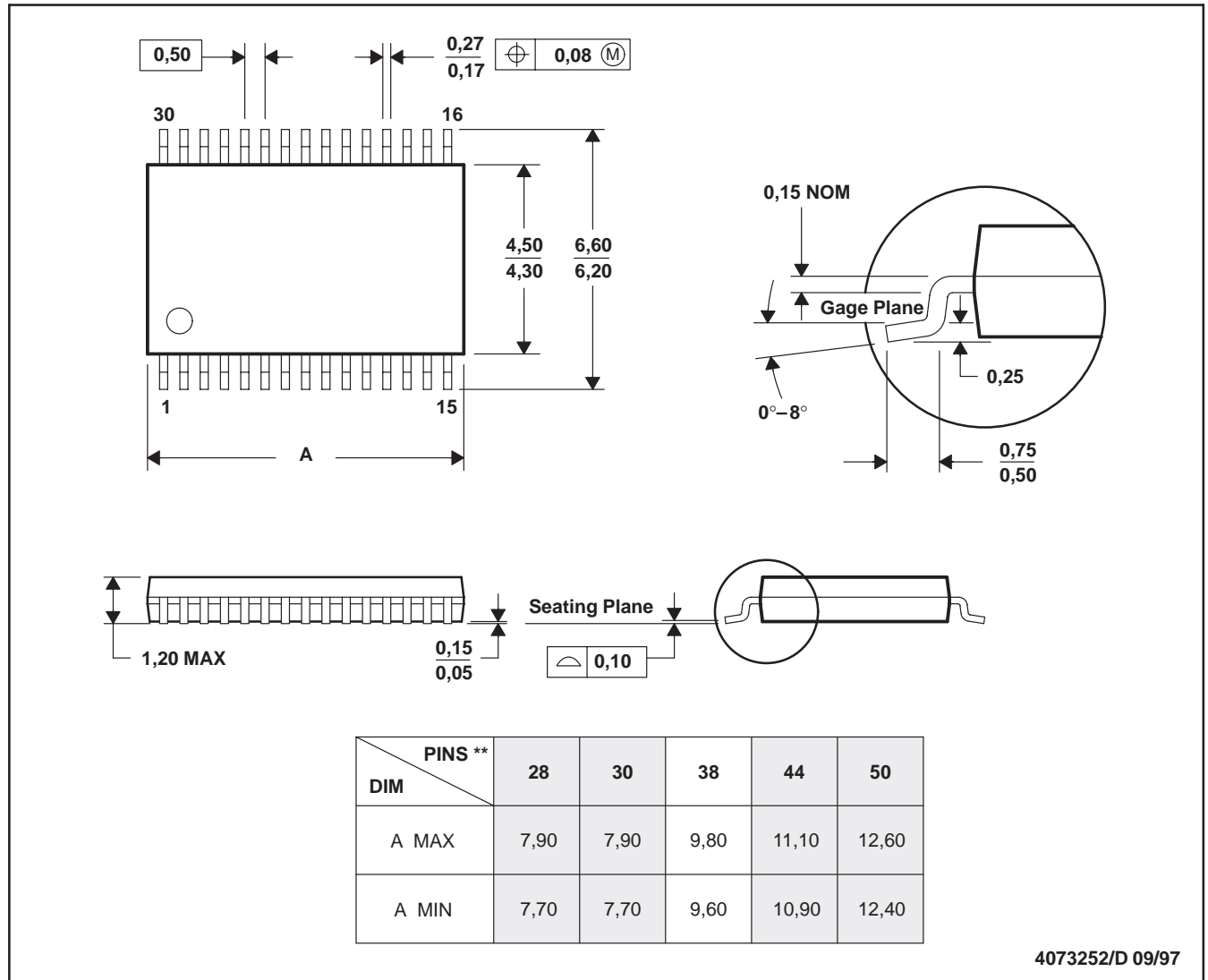
Figure 19. TTL

MECHANICAL DATA

DBT (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

30 PINS SHOWN



- NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion.
D. Falls within JEDEC MO-153

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